

# Louise Lilja

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4423937/publications.pdf>

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16  
papers

91  
citations

1936888

4  
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1588620

8  
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17  
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17  
docs citations

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times ranked

162  
citing authors

#	ARTICLE	IF	CITATIONS
1	Porous titania surfaces on titanium with hierarchical macro- and mesoporosities for enhancing cell adhesion, proliferation and mineralization. <i>Materials Science and Engineering C</i> , 2015, 47, 376-383.	3.8	25
2	Carrier Lifetime Controlling Defects $\langle i \rangle Z \langle /i \rangle \langle sub \rangle 1/2 \langle /sub \rangle$ and RB1 in Standard and Chlorinated Chemistry Grown 4H-SiC. <i>Crystal Growth and Design</i> , 2014, 14, 4104-4110.	1.4	14
3	The influence of growth conditions on carrier lifetime in 4H-SiC epilayers. <i>Journal of Crystal Growth</i> , 2013, 381, 43-50.	0.7	10
4	Wafer Scale On-Axis Homoepitaxial Growth of 4H-SiC(0001) for High-Power Devices: Influence of Different Gas Phase Chemistries and Growth Rate Limitations. <i>Crystal Growth and Design</i> , 2019, 19, 3288-3297.	1.4	7
5	Fast Growth Rate Epitaxy on $4^\circ$ Off-Cut 4-Inch Diameter 4H-SiC Wafers. <i>Materials Science Forum</i> , 0, 778-780, 179-182.	0.3	6
6	The Effect of Growth Conditions on Carrier Lifetime in N-Type 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 0, 717-720, 161-164.	0.3	4
7	Influence of Growth Temperature on Carrier Lifetime in 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2013, 740-742, 637-640.	0.3	4
8	In-grown stacking faults in 4H-SiC epilayers grown on $2^\circ$ off-cut substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 1319-1324.	0.7	4
9	On-Axis Homoepitaxial Growth of 4H-SiC PiN Structure for High Power Applications. <i>Materials Science Forum</i> , 0, 740-742, 173-176.	0.3	3
10	Improved Epilayer Surface Morphology on $2^\circ$ Off-Cut 4H-SiC Substrates. <i>Materials Science Forum</i> , 2014, 778-780, 206-209.	0.3	3
11	Comparison of Carrier Lifetime Measurements and Mapping in 4H SiC Using Time Resolved Photoluminescence and $^{14}$ PCD. <i>Materials Science Forum</i> , 0, 778-780, 301-304.	0.3	3
12	Oxidation Induced $ON_{1/2}$ , $ON_{2a/b}$ Defects in 4H-SiC Characterized by DLTS. <i>Materials Science Forum</i> , 2014, 778-780, 281-284.	0.3	2
13	Smooth 4H-SiC Epilayers Grown with High Growth Rates with Silane/Propane Chemistry Using $4^\circ$ Off-Cut Substrates. <i>Materials Science Forum</i> , 0, 858, 209-212.	0.3	2
14	Radial Variation of Measured Carrier Lifetimes in Epitaxial Layers Grown with Wafer Rotation. <i>Materials Science Forum</i> , 0, 717-720, 289-292.	0.3	1
15	Influence of Growth Mechanism on Carrier Lifetime in On-Axis Homoepitaxial Layers of 4H-SiC. <i>Materials Science Forum</i> , 2012, 717-720, 157-160.	0.3	1
16	Influence of n-Type Doping Levels on Carrier Lifetime in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 0, 897, 238-241.	0.3	1